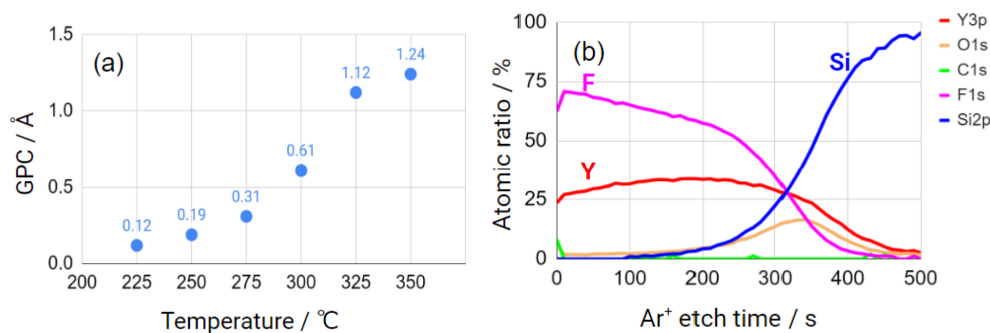
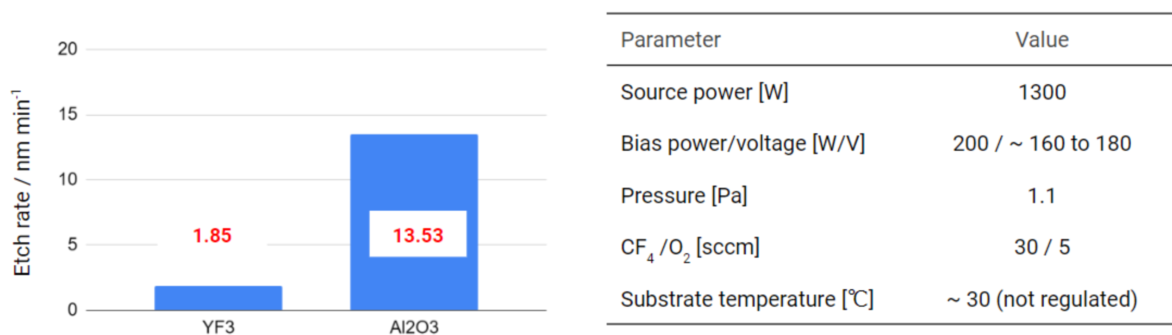


Figure 1. (a) The dependence of the GPC on the reactor temperature. The Y-beta prime precursor and O3 co-reactant are used for this experiment. (b) XPS depth profile of deposited film (the reactor temperature was 300℃).



Parameter	Value
Source power [W]	1300
Bias power/voltage [W/V]	200 / ~ 160 to 180
Pressure [Pa]	1.1
CF_4 /O_2 [sccm]	30 / 5
Substrate temperature [℃]	~ 30 (not regulated)

Figure 2. Etch rates of YF_3 thin film (35 nm) and Al_2O_3 thin film (500 nm). The Al_2O_3 film was provided by Beneq. The experiment conditions are summarized in the right table.